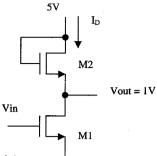
2. The MOS transistors M1 and M2 are identical. Given: $K = 10 \text{ mA/V}^2$ and $V_T = 1 \text{V}$.

$$I_D = K(V_{GS} - V_T)^2$$
 Saturation
$$I_D = 2K \left[(V_{GS} - V_T) V_{DS} - \frac{V_{DS}^2}{2} \right]$$
 Ohmic



- a) Find and prove the operation mode of M2. (6 marks)
- b) Calculate the current I_D (4 marks)
- c) Find Vin if M1 is in ohmic. (7 marks)
- d) Estimate the ON resistance ron of M1 (ron = $\partial V_{DS} / \partial I_D$). (5 marks)

$$0 > \sqrt{6} > \sqrt{7} > \sqrt{5} > \sqrt{4} > \sqrt{7} > \sqrt{6} > \sqrt{7} > \sqrt{6} > \sqrt{7} > \sqrt{7$$

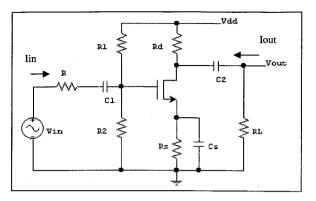
b)
$$I_b = K(v_{GS} - V_T)^2 = 10m (4-1)^2 = 90mA$$
 4

c)
$$I_D = 2k \left((V_{GS} - V_T) V_{DS} - \frac{V_{DS}^2}{2} \right)$$

 $90m = 2(10m) \left((V_{in} - 1) 1 - \frac{1}{2} \right)$
 $4.5 = V_{in} - 1.5$

d)
$$ron = \frac{1}{2k(v_{GS} - V_T)} = \frac{1}{2(10m)(6-1)}$$
= 10Ω

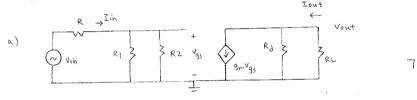
3. Given the following circuit diagram.



- a) Draw the ac equivalent circuit for the whole circuit. Assume C1, C2 and Cs are large, and r_0 of NMOS model is infinity. (7 marks)
- b) Find the total input resistance Rin (Rin = Vin / Iin).

(3 marks) (3 marks)

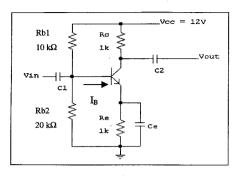
- c) Find the total output resistance Rout (Rout = Vout / Iout).
- d) Find the ac voltage gain of the amplifier (Av = Vout / Vin). The expression is required to be independent of Vin. (6 marks)



b)
$$R_{in} = \frac{V_{in}}{I_{in}} = R + R_1 || R_2$$

d) Av =
$$\frac{V_{\text{out}}}{V_{\text{in}}}$$
 = $\frac{-g_{\text{m}} V_{\text{gs}}}{V_{\text{gs}}}$ (Rd || RL)

12. Given the following circuit diagram.



$$\begin{split} \beta &= 50 \\ V_{CE} \text{ (sat)} &= 0.2 \text{ V} \\ V_{BE} &= 0.7 \text{ V} \end{split}$$

- a) Show that the base current I_B is 0.127 mA. (Hint: Use Thevenin's Theorem)
- (13 marks)

8

- b) Show that the Q-point is in the saturation region.c) Show that the forced β is 29.7 (18 marks)
- d) Suggest a method to move the Q-point to the active region. (4 marks)
- e) Give two advantages of this circuit connection.
- (4 marks)

(8 marks)

- f) Briefly explain the function of C1, C2 & Ce.
- (5 marks)

$$V_{B} = V_{cc} \frac{R_{b2}}{R_{b1} + R_{b2}} = \frac{12}{10K + 20K} = 8V$$
 3

$$\frac{1}{1} = \frac{V_{B} - V_{BE}}{R_{B} + (1 + \beta)R_{E}} = \frac{8 - 0.7}{\frac{20K}{3} + (1 + 50)1K}$$

$$= 0.127 \text{ mA}$$

b) If 81T active,
$$l_{c} = Bl_{B} = 50 (0.127 m)$$

= 6.33 mA $\approx l_{E}$
but $l_{c}R_{c} + l_{E}R_{E} \approx 6.33 m (2K)$
 $> 12 V$

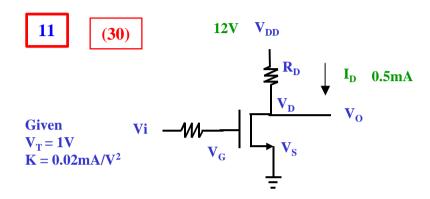
in BJT saturates

$$V_{CC} = I_{cR_{c}} + V_{cESAT} + I_{ER_{E}}$$
 $I_{B} = I_{cR_{c}} + V_{cESAT} + I_{ER_{E}}$
 $I_{B} = I_{cR_{c}} + V_{cESAT} + I_{ER_{E}}$

But
$$I_B$$
 also = $\frac{V_B - V_{BE}}{R_B + (1+ \beta_f)R_E} = \frac{8 - 0.7}{\frac{20k}{3} + (1+\beta_f)Ik}$

$$\therefore \beta_{f} = 24.7$$

$$(8)$$



Find R_D such that $Vi = V_O$, i.e. $V_{GS} = V_{DS}$ and NMOS saturates

:
$$I_{DS} = K (V_{GS} - V_T)^2 = 0.02m(V_{GS} - 1)^2 = 0.5mA$$

 $V_{GS} = \sqrt{\frac{0.5m}{0.02m}} + 1 = 6V$

$$V_{DD} = I_{DS}R_D + V_{DS}$$

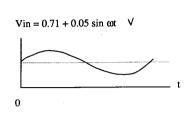
$$V_D = \frac{V_{DD} - V_{DS}}{I_{DS}} = \frac{12 - 6}{0.5m} = 12kW$$

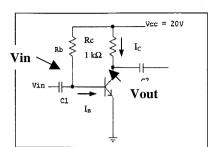
Find V_O such that $Vi=V_{DD}$ i.e. V_{GS} = 12V , hence V_{GS} - V_T > V_{DS} and NMOS in triode

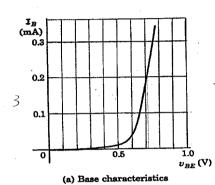
$$\begin{split} & \setminus I_{DS} = 2K[(V_{GS} - V_T)V_{DS} - \frac{{V_{DS}}^2}{2}] \\ & = 2(0.02m)[(12 - 1)V_{DS} - \frac{{V_{DS}}^2}{2}] \\ & \setminus I_{DS} = \frac{V_{DD} - V_{DS}}{R_D} = \frac{12 - V_{DS}}{12.5k} = 0.04m(11V_{DS} - \frac{{V_{DS}}^2}{2}) \\ & \setminus 12 - V_{DS} = 0.5[11V_{DS} - \frac{{V_{DS}}^2}{2}] \\ & \setminus 12 - 6.5V_{DS} + 0.25V_{DS}^2 = 0 \\ & \setminus V_{DS}^2 - 26V_{DS} + 48 = 0 \\ & \setminus V_{DS} = 24V \quad or \quad 2V \end{split}$$

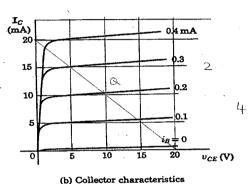
hence $V_O = V_{DS} = 2V$ (24 V > V_{DS} is impossible)

13. Given the following circuit diagram. The input (base) and output (collector) characteristics of the BJT are given.









- a) Plot the dc load line in the output characteristics. Show clearly your calculations. (4 marks)
- b) Show that the base current I_B is 0.2 mA. (3 marks)
- c) Calculate Rb. (3 marks)
- d) Show the location of the Q-point in the output characteristics. (2 marks)
- e) Find Ic and V_{CE} at the Q-point. (4 marks)
- f) Sketch the base current I_B , the collector current I_C and the output voltage Vout. Show clearly the dc level, the maximum and the minimum values in your sketch. (15 marks)
- g) Calculate the ac voltage gain (Av = Δ Vout / Δ Vin). (3 marks)
- h) Calculate the ac current gain (Ai = Δ Ic / Δ I_B).
- (3 marks)

3

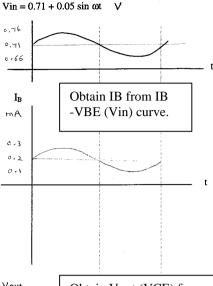
a)
$$V_{CC} = I_{C}R_{C} + V_{CE}$$

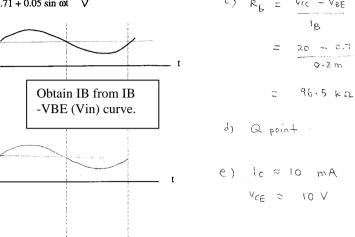
$$I_{C} = 0 \qquad V_{CE} = V_{CC} = 20V$$

$$V_{CE} = 0 \qquad I_{C} = \frac{V_{CC}}{R_{C}} = \frac{20V}{1K} = 20 \text{ mA}$$

$$V_{BE} \approx 0.7 V$$

$$V_{B} = 0.2 m A$$





f)

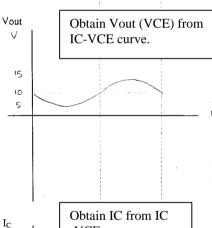
3

15

3

0.76 - 0.66

-100

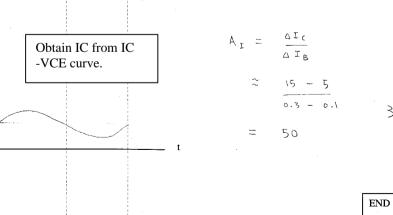


mA

15

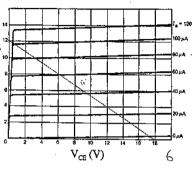
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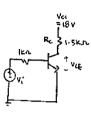
5



- 12. The BJT in the circuit has the output characteristic curves as shown.
- (a) Sketch the load line Vcc = IcRc + VcE, (6)
- (b) Locate the Q-point on the loadline and find the operating modes of the BJT (i) if Vi = 0.8V, and (ii) if the circuit is to give maximum symmetric VcE output. (14)
- (c) Show that the voltage gain $A_v (= \Delta Vo / \Delta Vi)$ of the circuit is -90. (11) Given that for the BJT, $V_{BE} = 0.7V$, $\beta = 120$, $r_{\pi} = 1 \text{ k}\Omega$, $r_0 = \infty$.





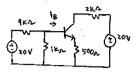


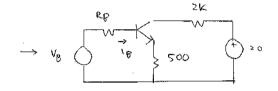
$$^{1}B = \frac{0.8 - 0.7}{1 \text{K}} = 0.1 \text{ m}$$

3

11. In the circuit, (a) show that $I_B \sim 25 \mu A$. (19) (b) Explain briefly why the circuit can have stable Ic. (7)

For the BJT, given $V_{RF} = 0.7V$ and $\beta = 100$.





$$A^{B} = 50 \frac{10K}{1K} = 5A$$

$$\frac{2 - 0.7}{900 + 101 (500)} = 25 \mu A \qquad 10$$